

Title (en)

PROCESS FOR PRODUCING THIN SINGLE CRYSTAL SILICON ISLANDS ON INSULATOR

Title (de)

VERFAHREN ZUR HERSTELLUNG DÜNNER EINZELKRISTALLSILICIUMINSELN AUF EINEM ISOLATOR

Title (fr)

PROCEDE DE PRODUCTION D'ILOTS DE SILICIUM MONOCRISTAUX MINCES SUR UN ISOLATEUR

Publication

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Application

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Abstract (en)

[origin: WO8805600A1] A semiconductor fabrication process uses an epitaxial layer (21) as an etch stop in a plasma etch process. In one embodiment, mechanical stops and an epitaxial layer are used in combination for stopping precisely at a desired end point.

IPC 1-7

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IPC 8 full level

H01L 21/301 (2006.01); **H01L 21/762** (2006.01)

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